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PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
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10/524,525INFORMATION DISCLOSURE
STATEMENT BY APPLICANTAPPLICANT
Martin Hausner

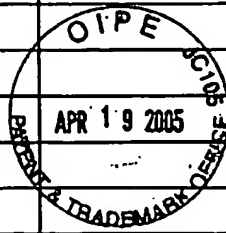
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FILING DATE
February 11, 2005CONFIRMATION NO.
1134

(37 CFR 1.98(b))

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A.A						
	A.B						
	A.C						
	A.D						
	A.E						
	A.F						
	A.G						
	A.H						
	A.I						
	A.J						
	A.K						



FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS

		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION (YES/NO)
/SA/	A.L	KR 2002041363A	06/2002	Republic of Korea	H01L	21/3065	No
	A.M						
	A.N						
	A.O						
	A.P						
	A.Q						

OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)

/SA/	A.R	Ayon et al., <u>Characterization of a Time Multiplexed Inductively Coupled Plasma Etcher</u> , Journal of the Electrochemical Society, January 1999, Vol. 146, Issue 1, pp. 339-349					
/SA/	A.S	The International Bureau of WIPO, <u>English Translation of the International Preliminary Examination Report</u> , November 17, 2004 (12 pages)					
	A.T						

EXAMINER

/Shamim Ahmed/ (04/11/2007)

DATE CONSIDERED

04/11/2007

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EV 2561458508

10/7/2005 25

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APPLICANT
Martin HausnerFILING DATE
February 11, 2005GROUP
Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER							ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
/SA/	A.A	6	0	7	4	9	4	6	06/2000	Ouellet et al.	438	689	02/1997
/SA/	A.B	6	4	5	8	6	1	5	10/2002	Fedder et al.	438	50	09/1999
	A.C												
	A.D												
	A.E												
	A.F												
	A.G												
	A.H												
	A.I												
	A.J												
	A.K												

FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS.

		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION (YES/NO)
/SA/	A.L	DE 196 41 288 A1	04/1998	Germany	C23F	4/00	No
	A.M	DE 197 36 370 C2	12/2001	Germany	H01L	21/3065	No
	A.N	DE 199 00 179 C1	02/2000	Germany	C23F	4/00	No
	A.O	DE 199 27 806 A1	01/2001	Germany	H01L	21/3065	No
	A.P	DE 44 20 962 C2	09/1998	Germany	H01L	21/308	No
/SA/	A.Q	JP 05021395 A	01/1993	Japan	H01L	21/302	Abstract Only

OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)

/SA/	A.R	Ayon et al., <u>Anisotropic silicon trenches 300-500 um deep employing time multiplexed deep etching (TMDE)</u> , Sensors and Actuators A, Vol. 91, 2001, pp. 381-385
/SA/	A.S	<u>Database WPI, A method of through-etching substrate is provided to efficiently perform a cooling processing of a substrate and to improve a profile around a penetrated hole by using a metal material</u> , Section Ch, Week 200278, Derwent Publications Ltd., London, GB, Class L03, AN 2002-720751 (1 page)
/SA/	A.T	Dijkstra et al., <u>Can SEA (Semiconductor Equipment Assessment) also deliver for MEMS?</u> , Horological Journal, Ashford, GB, Vol. 556, No. 302, 2001, pp. 684-690

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